SPECIFICATION AMENDMENTS

Replace the paragraph beginning at page 1, line 6 with:

The present invention relates to a semiconductor device having an interlayer insulating film disposed by ~~a~~ plasma CVD ~~method so as~~ to cover a metal wiring, and a method of manufacturing such a semiconductor device.

Replace the paragraph beginning at page 2, line 22 with:

~~Fig. 1 shows~~ Figs. 1A-1E show a method of manufacturing a semiconductor device according to the first embodiment of the present invention.

Replace the paragraph beginning at page 2, line 24 with:

~~Fig. 2 shows~~ Figs. 2A-2C show a method of manufacturing a semiconductor device according to the second embodiment of the present invention.

Replace the paragraph beginning at page 2, line 26 with:

~~Fig. 3 shows~~ Figs. 3A-3C show a method of manufacturing a semiconductor device according to the third embodiment of the present invention.

Replace the paragraph beginning at page 2, line 28 with:

~~Fig. 4 shows~~ Figs. 4A-4C show a method of manufacturing a semiconductor device according to the fourth embodiment of the present invention.

Replace the paragraph beginning at page 2, line 30 with:

~~Fig. 5 shows~~ Figs. 5A-5C show a method of manufacturing a semiconductor device according to the fifth embodiment of the present invention.

Replace the paragraph beginning at page 3, line 3 with:

~~Fig. 1 shows~~ Figs. 1A-1E show a method of manufacturing a semiconductor device according to the first embodiment of the present invention. First, as Fig. 1A shows, a Ti film

2, which is the film of a high-melting-point metal; an Al wiring 3, which is a metal wiring; and a Ti film 4, which is the film of a high-melting-point metal are sequentially deposited on a substrate 1 consisting of Si or the like. At this time reactive layers are formed in the interfaces between the Ti film 2 and the Al wiring 3, and the Al wiring 3 and the Ti film 4. The thickness of each of the Ti films 2 and 4 is about 2.0 nm to about 5.0 nm.

Replace the paragraph beginning at page 5, line 19 with:

~~Fig. 2 shows~~ Figs. 2A-2C show a method of manufacturing a semiconductor device according to the second embodiment of the present invention. The same constituents as shown in ~~Fig. 1~~ Figs. 1A-1E are denoted by the same reference numerals, and the description thereof will be omitted. First, as Fig. 2A shows, an Al wiring 3 covered with Ti films 2 and 3 immediately above and below, respectively, is formed on a substrate 1.

Replace the paragraph beginning at page 6, line 25 with:

~~Fig. 3 shows~~ Figs. 3A-3C show a method of manufacturing a semiconductor device according to the third embodiment of the present invention. The same constituents as shown in ~~Fig. 1~~ Figs. 1A-1E are denoted by the same reference numerals, and the description thereof will be omitted. First, as Fig. 3A shows, an Al wiring 3 is formed on a substrate 1.

Replace the paragraph beginning at page 7, line 28 with:

~~Fig. 4 shows~~ Figs. 4A-4C show a method of manufacturing a semiconductor device according to the fourth embodiment of the present invention. The same constituents as shown in ~~Fig. 1~~ Figs. 1A-1E are denoted by the same reference numerals, and the description thereof will be omitted. First, as Fig. 4A shows, an Al wiring 3 is formed on a substrate 1.

Replace the paragraph beginning at page 8, line 28 with:

~~Fig. 5 shows~~ Figs. 5A-5C show a method of manufacturing a semiconductor device according to the fifth embodiment of the present invention. The same constituents as shown in ~~Fig. 1~~ Figs. 1A-1E are denoted by the same reference numerals, and the description thereof will be omitted. First, as Fig. 5A shows, an Al wiring 3 is formed on a substrate 1.